

Commodity Specification

C.S. No.	Rev.	Date
RCS-MM-12485	0	Apr. 24, 2009

Apple Inc.

Type
R5H30201NA04NQ09
(Pb-Free T.)

※【RoHS compliant】Pb-FreeT. means product keeps terminals treated by Lead Free materials.

Signed

NOTICE

Please check this C.S. and return this copy with your signature to acknowledge your approval.

Starting from April 1, 2003, Renesas Technology Corp. takes over the responsibility for attached drawings from Hitachi, Ltd., due to the corporate division.

RENESAS
Renesas Technology Corp.

MCU Business Group

Tatsumi Sueyoshi

Cautions

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 - (3) healthcare intervention (e.g., excision, administration of medication, etc.)
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8. In case Renesas products listed in this document are detached from the products to which the Renesas products are attached or affixed, the risk of accident such as swallowing by infants and small children is very high. You should implement safety measures so that Renesas products may not be easily detached from your products. Renesas shall have no liability for damages arising out of such detachment.
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Absolute Maximum Ratings

Table 1 Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Power supply voltage	V_{CC}	-0.3 to +7.0	V
Input voltage	V_{in}	-0.3 to $V_{CC} + 0.3$	V
Operating temperature	T_{opr}	-25 to +85	°C
Storage temperature	T_{stg}	-55 to +85	°C

Note: Permanent damage may occur to the chip if maximum ratings are exceeded. Normal operation should be under the recommended operating conditions. Exceeding these conditions could affect the reliability of the chip.

DC Characteristics

Table 1 DC Characteristics

 Conditions: $V_{CC} = 1.8$ to 3.6 V, $V_{SS} = 0$ V, $T_a = -25$ to $+85^\circ\text{C}$, unless otherwise specified.

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Input high voltage $\overline{\text{RES}}$ P1, P2, P3, P4	V_{IH}	$V_{CC} = 1.8$ to 2.2 V	$V_{CC} \times 0.85$	—	$V_{CC} + 0.3$	V
		$V_{CC} = 2.2$ to 3.6 V	$V_{CC} \times 0.7$	—	$V_{CC} + 0.3$	
Input low voltage $\overline{\text{RES}}$ P1, P2, P3, P4	V_{IL}	$V_{CC} = 1.8$ to 2.2 V	-0.3	—	0.2	V
		$V_{CC} = 2.2$ to 3.6 V	-0.3	—	$V_{CC} \times 0.2$	
Output high voltage P1, P2, P3, P4	V_{OH}	$I_{OH} = -200$ μA	$V_{CC} \times 0.7$	—	V_{CC}	V
Output low voltage I/O ports	V_{OL}	$I_{OL} = 1$ mA	0	—	0.4	V
Input leakage current P1, P2, P3, P4	$ I_{in} $	$V_{in} = 0.5$ to $V_{CC} - 0.5$ V	—	—	10	μA
Input pull-up MOS current* ¹ $\overline{\text{RES}}$ P1, P2, P3, P4	$-I_p$	$V_{in} = 0$ V	—	—	150	μA
			—	—	150	
Supply Current* ² CPU half of the external clock/ external clock	I_{CC}	Coprocessor stops* ³	—	—	7.5	mA
		CPU multiplied by one with PLL Exclusive mode* ³	—	—	7.5	
		CPU multiplied by two with PLL Normal speed of coprocessor in maximum mode* ³	—	—	7.5	
Supply Current* ² Sleep mode 1	I_{CC}	V_{in} (I/O ports and $\overline{\text{RES}}$) = $V_{CC} - 0.5$ V to V_{CC} or I/O ports open* ¹ $T_a \leq 50^\circ\text{C}$	—	—	100	μA
		V_{in} (I/O ports and $\overline{\text{RES}}$) = $V_{CC} - 0.5$ V to V_{CC} or I/O ports open* ¹ $T_a \geq 50^\circ\text{C}$	—	—	200	
Pin capacitance	C_p	$V_{in} = 0$ V, $f_{CLK} = 1$ MHz, $T_a = 25^\circ\text{C}$	—	—	15	pF

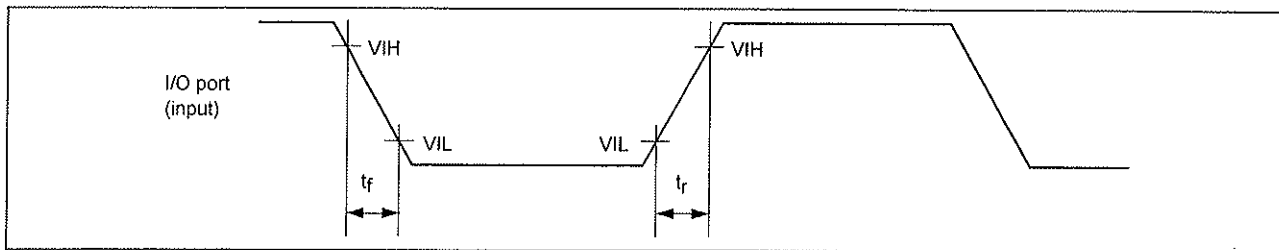
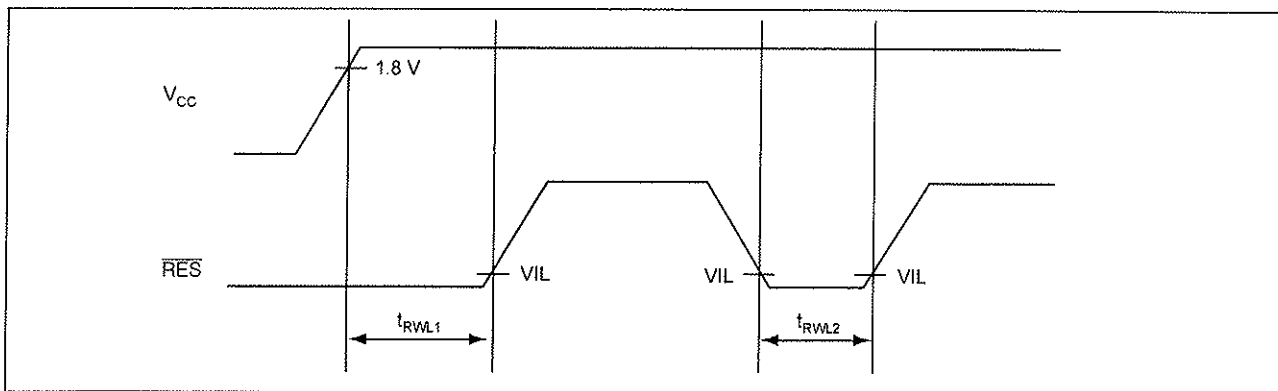
- Notes: 1. The input pull-up MOS's in the $\overline{\text{RES}}$ is always turned on, even in sleep mode 1 and sleep mode 2. To avoid the input pull-up MOS current, the $\overline{\text{RES}}$ must be kept high during sleep mode 1 and sleep mode 2.
2. $V_{IHmin} = V_{CC} - 0.5$ V, $V_{ILmax} = 0.5$ V, and values are when all output pins are unloaded.
3. These are operating modes other than sleep mode 1.

AC Characteristics

Table 1 AC Characteristics

Conditions: $V_{CC} = 1.8$ to 3.6 V, $V_{SS} = 0$ V, $T_a = -25$ to $+85^\circ\text{C}$, unless otherwise specified.

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Clock cycle time (CPUCS = 0)	t_{cyc}		278	333	417	ns	
Clock cycle time (CPUCS = 1)			139	166	208		
Clock rise time	t_{cr}	Figure 1	—	—	1.0	μs	
I/O port input fall time	t_f	Figure 1	—	—	1.0	μs	
RES pulse width	Cold reset	t_{RWL1}	Figure 2	500	—	μs	
	Warm reset	t_{RWL2}	Figure 2	400	—	t_{cyc}	
EEPROM write time	Normal rewriting mode	Rewrite	t_{EPW}	—	—	3	ms
		Erase		—	—	1.5	ms
Interrupt pulse width (IRQ)	Sleep mode 2	t_{IRQW}	Figure 3	4	—	t_{cyc}	
	Other modes			400	—	ns	


Figure.1 I/O Port Input Waveform

Figure.2 Power ON/OFF and RES Input Timing

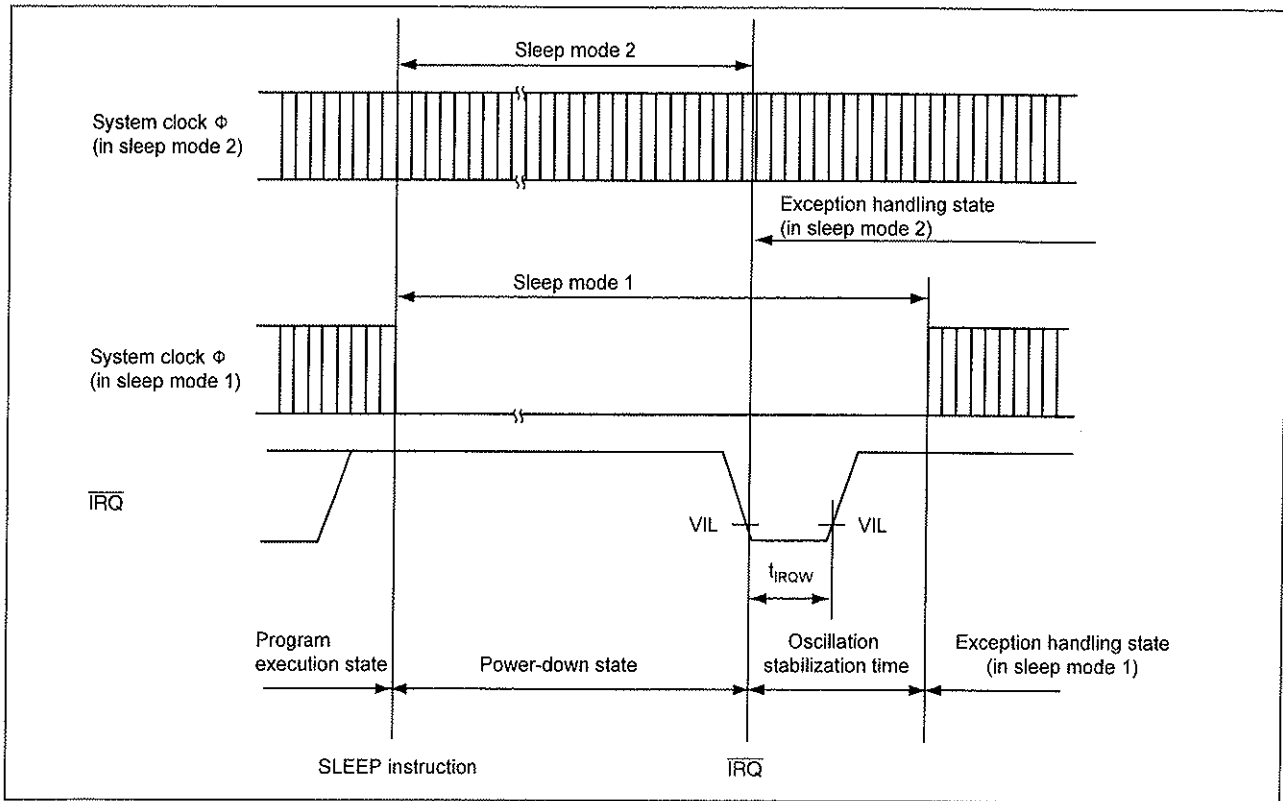


Figure 3 Interrupt Timing in Sleep Mode 1 and Sleep Mode 2

Reset Circuit Characteristics

Table 1 Reset Circuit Characteristics

Conditions: $V_{CC} = 1.8$ to 3.6 V, $V_{SS} = 0$ V, $T_a = -25$ to $+85^\circ\text{C}$, unless otherwise specified.

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Power-on reset effective voltage	V_{POR1}	Figure 1	—	—	0.1	V
Power-on reset release voltage rise time	t_{PWON1}	Figure 1 $t_{POR1} \geq 1\text{s}^*$	—	—	0.5	ms
Power-on reset release voltage rise time	t_{PWON1}	Figure 1 $t_{POR1} \geq 10\text{s}^*$	—	—	1	ms
Power-on reset release time	t_{PRST}	Figure 1	—	—	500	μs

Note: t_{POR1} is the time needed to enable the power-on reset by keeping the external power supply V_{CC} to lower than the effective voltage (V_{POR1}).

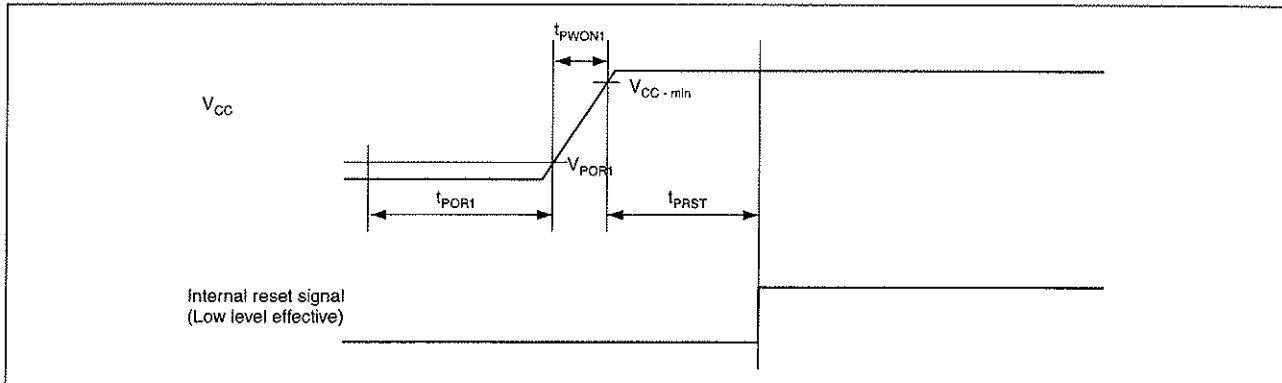


Figure 1 Power-On Reset Timing

Voltage Monitoring Circuit

Table 1 Voltage Monitoring Circuit Characteristics

Conditions: $V_{CC} = 1.8$ to 3.6 V, $V_{SS} = 0$ V, $T_a = -25$ to $+85^\circ\text{C}$, unless otherwise specified.

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Voltage detect level	V_{DETO}	Figure 1	1.9	2.3	2.6	V

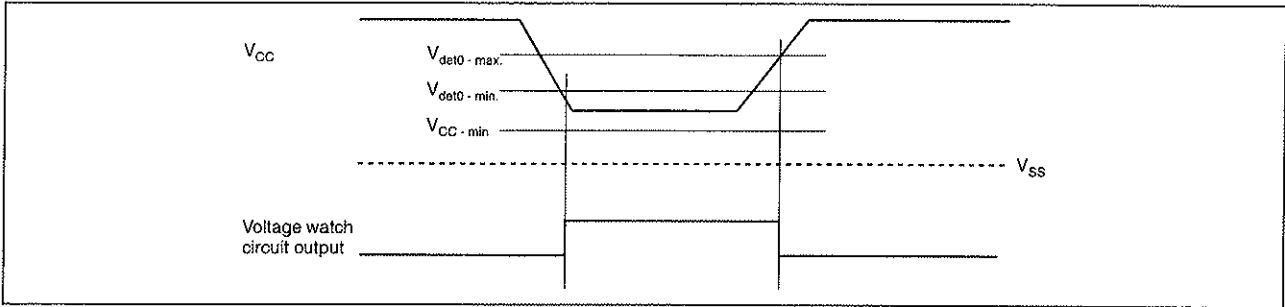


Figure 1 Voltage Monitoring Circuit Timing

Erase/Write cycle endurance and Data retention time of EEPROM are specified as follows.

Item	Condition	Rating
Erase/Write cycle endurance of EEPROM *1	Page rewrite *2 -25°C to +85°C	1 x 10 ⁵ times
Data retention time		10 years

Note; *1 It is assumed the failure rate is 1% or below in case of reliability standard 90%.

*2 One page rewriting is counted as one time.

Block Diagram

Figure 1 is a block diagram of this LSI.

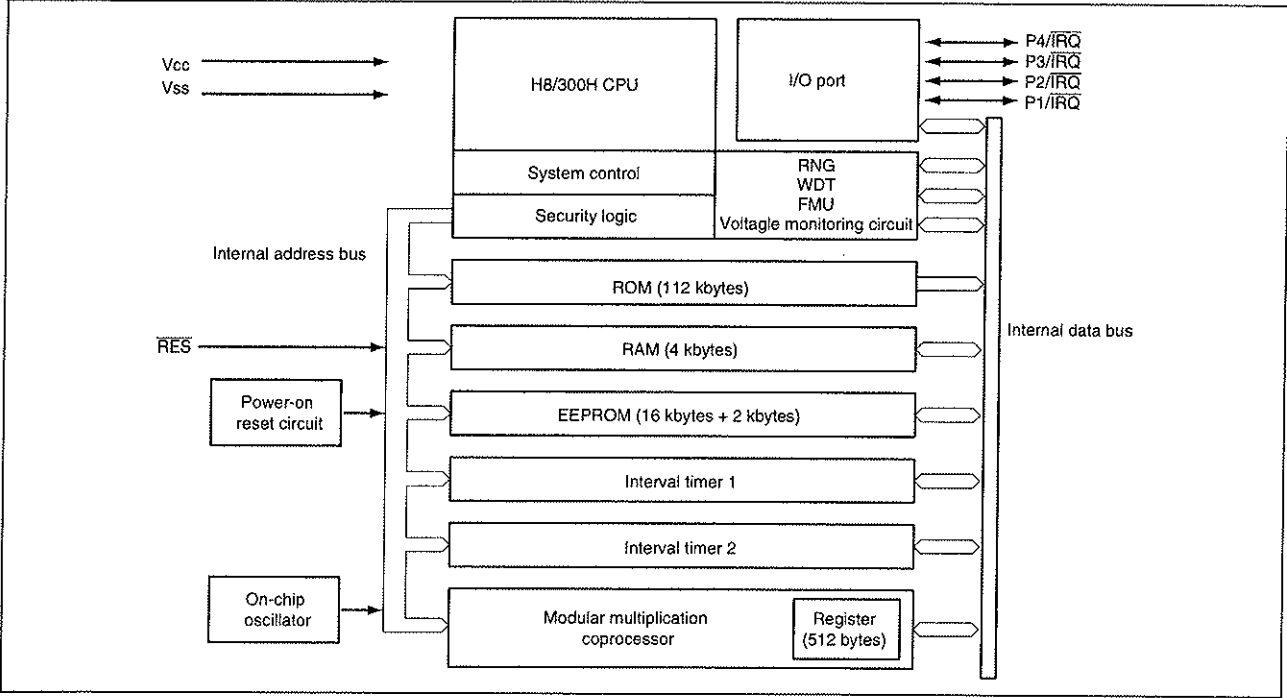


Figure 1 Block Diagram

Pin Assignment

Figure 1 shows the pin arrangement of this LSI.

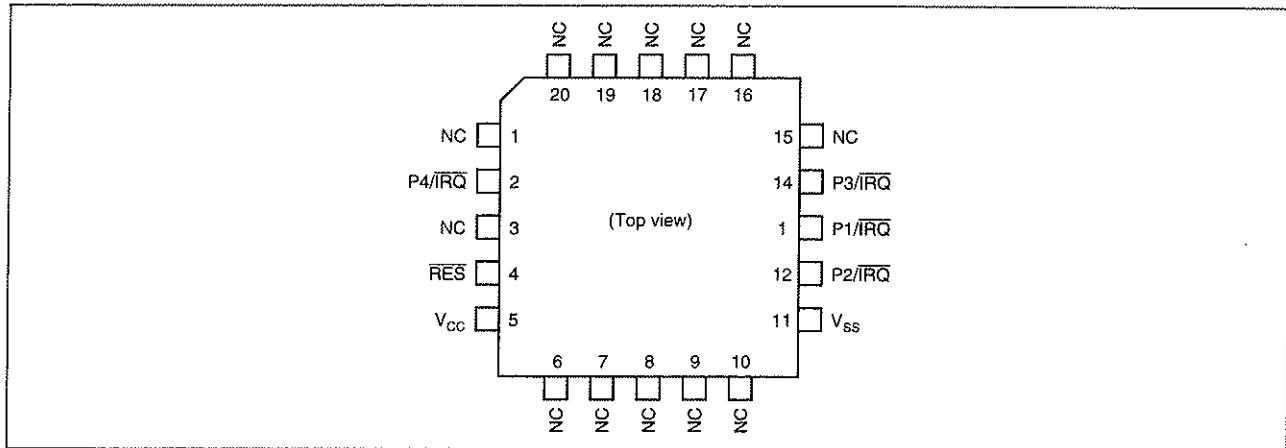
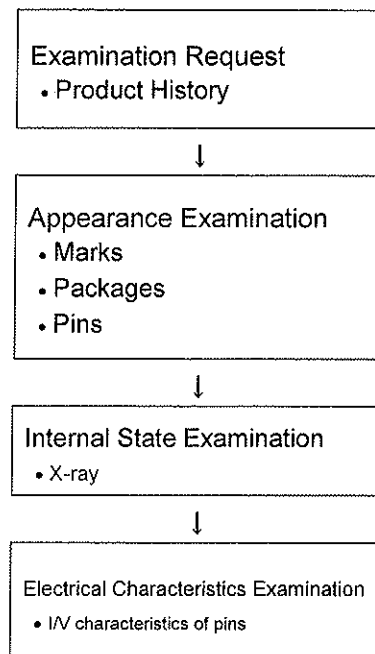


Figure 1 Pin Assignment (TNP-20CV)

Returns Analysis

This product has an advanced security function against unauthorized attacks. Therefore, unlike common MCU products, it is impossible to carry out a functional test with an LSI tester against shipped products.

Returns analysis flow chart of this product is illustrated below.

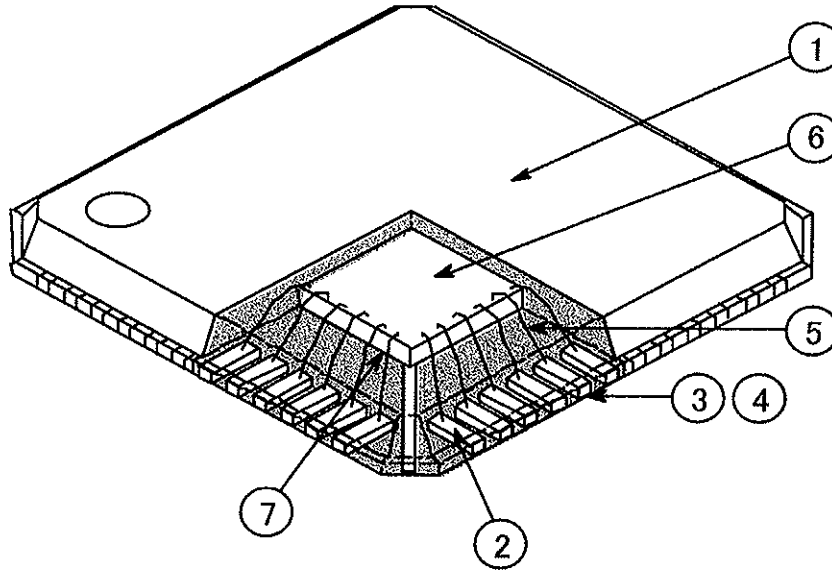


Returns Analysis Flow Chart
(Examination and Evaluation Method)

DATE REVD. CHKD. APPD.
REVISIONS

SYM. APL

QFN内部構造図 (QFN Internal structure)



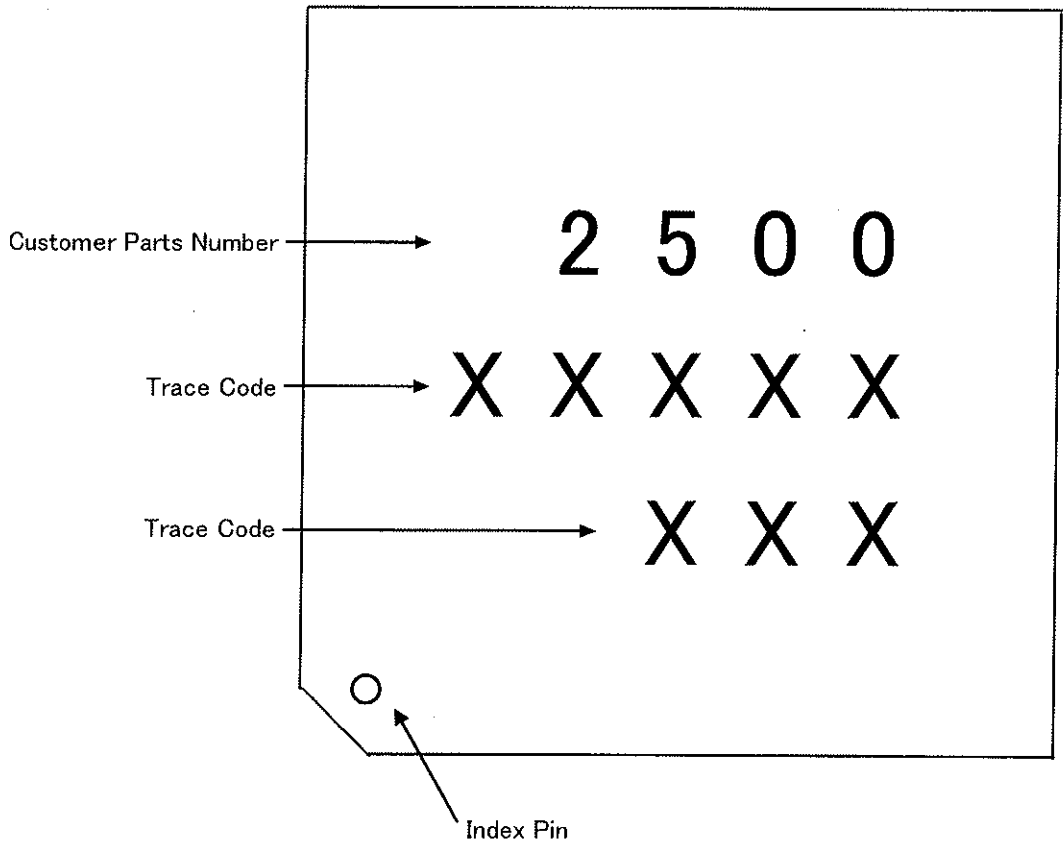
番号 (No.)	部分 (Part)	材質 (Material)
①	封止樹脂 (Molding compound)	エポキシ樹脂 難燃性レベル (Epoxy) (UL-level) UL-94V0
②	インナーリード処理 (Inner lead finish)	ニッケル/パラジウム/金 めっき (Ni/Pd/Au plating)
③	アウターリード処理 (Outer lead finish)	ニッケル/パラジウム/金 めっき (Ni/Pd/Au plating)
④	リード (Lead)	銅合金 (Copper Alloy)
⑤	ボンディングワイヤ (Bonding wire)	金 (Gold)
⑥	チップ (Die)	シリコン (Silicon)
⑦	ダイボンディング材 (Die bonding)	樹脂ペースト (Organic adhesive)

MM5 1
MQ 1
PROVI. co
SECT. py

REMARKS		PROJECTION		TITLE		DWG. STAMP	
DWN.				FTR-STRCT			
CHKD.		SCALE		QFN内部構造図			
APPD.		NTS					
		REGD.		SD	TYPE	D.D	CLASS.
				E	03	AN	528
				MD	WORK-SPEC No.		
				E	PKGFTR		
							1228
		Renesas Technology Corp.				SH.	
		343 4Q02214				1	
						E	

D.CHKD

D C B A QFN Gr. PKG



To: AVNET _____

Preliminary

RENESAS
Date: 2008/1/31

Investigation by Renesas standard format on constituents of products(Reply)

Please find below information on all constituents of our semiconductor product R5H30201NA04NQXX (Renesas part no.). If you require this information to be provided in the format designated by you, please inform our sales department of your request. In this case, we ask that you give us an extra time to meet your requirements. We confirm that the materials stipulated in Montreal Protocol (Level 1) have not been used in the production of R5H30201NA04NQXX (Renesas part no.).

We also confirm that the product does not include any of the materials stipulated in EU RoHS Directives.

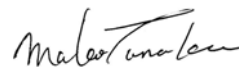
CH07-2132

PART	SUBSTANCE	CAS_NO	RENE_CODE	MASS_MG	RATIO	RATIO_P	PURPOSE
chip	Silicon	7440-21-3	C020001	4.064948	11.6000	99.4000	wafers
chip	Arsenic	7440-38-2	C030001	0.000020	0.0001	0.0005	dopant
chip	Boron	7440-42-8	C040001	0.000409	0.0012	0.0100	dopant et.al.
chip	Phosphorus	7723-14-0	C050003	0.001023	0.0029	0.0250	dopant et.al.
chip	Copper	7440-50-8	C160001	0.000123	0.0004	0.0030	wiring material
chip	Aluminum	7429-90-5	C210001	0.024546	0.0701	0.6000	wiring material
			sub_total	4.091070	11.7000	100.0000	
leadframe	Nickel	7440-02-0	C150001	0.257318	0.7350	2.0900	alloy,inner plating
leadframe	Copper	7440-50-8	C160001	12.028237	34.4000	97.6000	alloy,plating
leadframe	Tin	7440-31-5	C260001	0.012064	0.0345	0.0979	alloy,lead finish
leadframe	Palladium	7440-05-3	C310006	0.021360	0.0610	0.1730	inner plating
leadframe	Gold	7440-57-5	C310010	0.003390	0.0097	0.0275	inner plating
			sub_total	12.322369	35.2000	100.0000	
die bonding	Silver	7440-22-4	C170001	0.072360	0.2070	80.4000	electric conductor
die bonding	Epoxy resin	none	C670001	0.017640	0.0504	19.6000	adhesive
			sub_total	0.090000	0.2570	100.0000	
wires	Gold	7440-57-5	C310010	0.029089	0.0831	100.0000	wiring
			sub_total	0.029089	0.0831	100.0000	
encapsulation	Fused quartz	60676-86-0	C020013	14.429712	41.2000	78.1000	chief element
encapsulation	Other organic phosphorus compounds	298-00-0 etc.	C339999	0.048960	0.1400	0.2650	hardening
encapsulation	Epoxy resin	none	C670001	3.988800	11.4000	21.6000	base resin
			sub_total	18.467472	52.8000	100.0000	
			grand_total	35.000000	100.0000	0.0000	eQ019980.dbf SQ019980.DBF

PART : components, RENE_CODE : Our control no., MASS_MG : mass (mg)
RATIO : wt% on the total mass, RATIO_P : wt% on each site's mass
ppm on the total mass = RATIO x 10000 ppm on each part's mass= RATIO_P x 10000

*This data is called IMDS(International Material Data System) data calculated from designed data.
It shows 100 percent content of intentionally contained substances.

Sincerely Yours,
Renesas Technology Corporation



Makoto Tanaka
Manager
Corporate Environment and Safety Strategic Planning Dept.

To: Apple Inc.

Renesas Technology Statement Regarding the Registration, Evaluation,
Authorization and Restriction of Chemicals (REACH)

This document is Renesas Technology's statement regarding Regulation (EC) No 1907/2006 of European Parliament and of the Council of 1 June 2007 concerning the Registration, Evaluation, Authorization, and of Restriction of Chemicals (REACH).

Renesas part (product) number:

R5H30201NA04NQ01GZ, R5H30201NA04NQ03GZ
R5H30201NA04NQ07GZ, R5H30201NA04NQ08GZ,
R5H30201NA04NQ09GZ, R5H30201DA04SP03

We hereby declare that products manufactured by Renesas Technology do not contain substances on the REACH SVHC candidate list in the table below.

Table 1. Candidate List of Substances of Very High Concern (SVHC)

No	Substance name	CAS number	EC number
1	Anthracene	120-12-7	204-371-1
2	4,4'-Diaminodiphenylmethane	101-77-9	202-974-4
3	Dibutyl phthalate	84-74-2	201-557-4
4	Cobalt dichloride	7646-79-9	231-589-4
5	Diarsenic pentaoxide	1303-28-2	215-116-9
6	Diarsenic trioxide	1327-53-3	215-481-4
7	Sodium dichromate	7789-12-0	234-190-3
8	5-tert-butyl-2,4,6-trinitro-m-xylene (musk xylene)	81-15-2	201-329-4
9	Bis(2-ethyl(hexyl)phthalate) (DEHP)	117-81-7	204-211-0
10	Hexabromocyclododecane (HBCDD) and all major diastereoisomers identified (α -HBCDD, β -HBCDD, γ -HBCDD)	25637-99-4	247-148-4
11	Alkanes, C10-13, chloro (Short Chain Chlorinated Paraffins)	85535-84-8	287-476-5
12	Bis(tributyltin)oxide	56-35-9	200-268-0
13	Lead hydrogen arsenate	7784-40-9	232-064-2
14	Benzyl butyl phthalate	85-68-7	201-622-7
15	Triethyl arsenate	15606-95-8	427-700-2

Renesas Technology Corporation



Nobuyuki Ishii
Senior Engineer
Corporate Environment and Safety Strategic Planning Dept.
CSR Management Div.
Date: 16 April 2009

Report No. MAR-6001

Date : Oct. 3rd. 2008

To : Apple Inc.

RENESAS SEMICONDUCTOR
RELIABILITY REPORT

DEVICE : R5H30201NA04NQ Series

APPLICATION : Consumer

Reported by M. Ishiyama
M. Ishiyama

Confirmed by A. Nakanishi
A. Nakanishi

Approved by Y. Hosokawa
Y. Hosokawa

MCU Quality Assurance Dept.
Quality Assurance Div.
Renesas Technology Corp.

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 - (4) any other purposes that pose a direct threat to human lifeRenesas shall have no liability for damages arising out of the uses set forth in the above and purchasers who elect to use Renesas products in any of the foregoing applications shall indemnify and hold harmless Renesas Technology Corp., its affiliated companies and their officers, directors, and employees against any and all damages arising out of such applications.
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1. INTRODUCTION

R5H30201NA04NQ Series are devices developed with Renesas 0.18um CMOS design rule, wafer process and Renesas standard package. This reliability report is the summary of the reliability test results at development and production of this device.

2. MAIN FEATURE

Product name	Type	Outline	Operating voltage	Use
16bit Smartcard MCU	R5H30201NA04NQ01	VQFN (PVQN0020KB-A)	Vcc=1.8~3.6V (1~10MHz)	Consumer
	R5H30201NA04NQ02			
	R5H30201NA04NQ03			
	R5H30201NA04NQ04			
	R5H30201NA04NQ05			
	R5H30201NA04NQ06			
	R5H30201NA04NQ07			
	R5H30201NA04NQ08			

3. FAILURE RATE

The failure rate is estimated as follows.

81 FIT

Where : • Ta = 40C • Ea = 0.8eV • Confidence Level = 60%

4. TEST RESULT

Test Name	Pre	Test Condition	Test Result NG (ps) / Test (ps)	Addition
High Temperature Operating Life		Ta=100C, Vcc=3.6V, t=1000h	0/96	
High Temperature storage		Ta=150C, t=1000h	0/22	
Low Temperature storage		Ta=-55C, t=1000h	0/22	
Temperature Humidity storage	*1	Ta=85C, RH=85%, t=1000h	0/22	
Temperature Humidity Bias	*1	Ta=85C, RH=85%, Vcc=3.6V, t=1000h	0/22	
Pressure Cooker Test	*1	Ta=121C, RH=100%, t=100h	0/22	Reference
Temperature Cycle	*1	-55C~150C, 1000cycles	0/22	
Thermal Shock		0C~100C, 100cycles	0/22	
Electric-Static Discharge	HBM	R=1.5kΩ, C=100pF, +/-2000V, once	0/5	
	CDM	+/-1000V, once	0/5	
	MM	R=0Ω, C=200pF, +/-200V, once	0/5	Reference
Latch-up(Pulse Current Injection)		I= +/-150mA	0/5	
Solderability		245C, Rosin type flux, t=5s	0/22	
Drop		h=0.75m, Maple tree board, 3times	0/22	
Resistance to Soldering Heat	*2	Infrared Reflow Soldering 255C, 30s, 3times (MAX260C)	0/22	
	*2	Air Reflow Soldering 255C, 30s, 3times (MAX260C)	0/22	
	*2	Package dipping, 260C, t=10s, 3times	0/22	
		Leads dipping, 350C, t=3s	0/22	
Program/Erase Cycling		85C, 100k cycles	0/66	
Data Retention	*3	85C, t=1000h	0/22	
	*3	25C, t=1000h	0/22	
	*3	-20C, t=1000h	0/22	

*) All electrical tests before and after the reliability tests are based on the individual product specification.

*1 Pretreatment Condition : 85°C65%RH24h+Infrared Reflow Soldering 255C, 30s, 3times (MAX260C)

*2 Pretreatment Condition : 85°C65%RH24h

*3 Pretreatment Condition : Program/Erase Cycling 100k cycles at 85C